



TECHNICAL SPECIFICATIONS

Output stage: bipolar/MOSFET class H device
Output stage power supply (max) $\pm 130V$
Power supply filter capacity 94 000 μF

Output power (1 KHz/THD = 1%)
into 8 Ω 2x850 W
into 4 Ω 2x1500 W
into 8 Ω bridged 1x3000 W

Output power (20 Hz ÷ 20 KHz /THD = 0.2%)
into 8 Ω 2x770 W
into 4 Ω 2x1360 W
into 8 Ω bridged 1x3000 W

Dynamic power (1 ch, 1 KHz, 4 Ω , 50 ms) 1850 W
Frequency response (+0dB, -1dB) 10 Hz ÷ 20 KHz
Max. output level (1 KHz, THD 1%, no load) 88V RMS
Voltage gain 33 dB
Input sensitivity +6 dB (1.55 V)
Max. input level +21 dB (8.7 V)
Input impedance 10 k Ω
THD (20 Hz ÷ 20 KHz, -3 dB) $\leq 0.1\%$
IMD - SMPTE (60 Hz, 7 KHz, -3 dB) $\leq 0.03\%$
Rise time $\leq 7 \mu s$
Slew rate (into 8 Ω load) 40V/ μs
Damping factor (into 8 Ω , 20 Hz ÷ 1 KHz) ≥ 200
Signal/noise ratio ≥ 98 dB
DC output offset ± 10 mV
Protections short circuit, DC out, thermal cut off,
limiter, slow start

Cooling variable speed DC fan
AC power consumption (max) 220V/50Hz, 3520 W
Dimensions 483x132x450 mm
Weight 26 kg

